

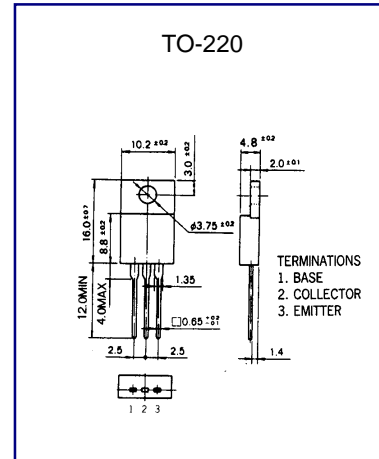


2SB507

PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SD313



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-60	V
Collector-Emitter Voltage	VCEO	-60	V
Emitter-Base voltage	VEBO	-7	V
Collector Current (DC)	IC	-3	A
Collector Dissipation (Tc=25°C)	PC	30	W
Junction Temperature	Tj	150	25°C
Storage Temperature	Tstg	-50~150	25°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	VCB= -60V , IE=0			-100	μA
Emitter Cutoff Current	IEBO	VEB= -7V , IC=0			-100	μA
DC Current Gain	hFE1	VCE= -2V , IC=-1A	40		320	
Collector- Emitter Saturation Voltage	VCE(sat)	IC=-2A , IB=-0.2A			-1.0	V
Current Gain Bandwidth Product	fT	VCE=- 5V , IC=-0.5A		8		MHZ